

DATA SHEET

74LVC3G04 Triple inverter

Preliminary specification
File under Integrated Circuits, IC24

2003 Aug 19

Triple inverter**74LVC3G04****FEATURES**

- Wide supply voltage range from 1.65 to 5.5 V
- 5 V tolerant outputs for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
 - JESD8-7 (1.65 to 1.95 V)
 - JESD8-5 (2.3 to 2.7 V)
 - JESD8B/JESD36 (2.7 to 3.6 V)
- ESD protection:
 - HBM EIA/JESD22-A114-A exceeds 2000 V
 - MM EIA/JESD22-A115-A exceeds 200 V
- ± 24 mA output drive ($V_{CC} = 3.0$ V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- SOT505-2 and SOT765-1 package
- Specified from -40 to $+125$ °C.

DESCRIPTION

The 74LVC3G04 is a high-performance, low-power, low-voltage, Si-gate CMOS device and superior to most advanced CMOS compatible TTL families.

Inputs can be driven from either 3.3 or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 and 5 V environment.

This device is fully specified for partial power-down applications using I_{off} . The I_{off} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74LVC3G04 provides three inverting buffers.

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25$ °C.

SYMBOL	PARAMETER	CONDITIONS	TYP.	UNIT
t_{PHL}/t_{PLH}	propagation delay inputs nA to output nY	$V_{CC} = 1.8$ V; $C_L = 30$ pF; $R_L = 1$ kΩ	3.5	ns
		$V_{CC} = 2.5$ V; $C_L = 30$ pF; $R_L = 500$ Ω	2.2	ns
		$V_{CC} = 2.7$ V; $C_L = 50$ pF; $R_L = 500$ Ω	2.7	ns
		$V_{CC} = 3.3$ V; $C_L = 50$ pF; $R_L = 500$ Ω	2.7	ns
		$V_{CC} = 5.0$ V; $C_L = 50$ pF; $R_L = 500$ Ω	1.9	ns
C_I	input capacitance		2.5	pF
C_{PD}	power dissipation capacitance per gate	$V_{CC} = 3.3$ V; notes 1 and 2	13.5	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

N = total switching outputs;

$$\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs.}$$

2. The condition is $V_I = \text{GND}$ to V_{CC} .

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FUNCTION TABLE

See note 1.

INPUTS		OUTPUTS	
nA		nY	
L		H	
H		L	

Note

1. H = HIGH voltage level;

L = LOW voltage level.

ORDERING INFORMATION

TYPE NUMBER	PACKAGES					
	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE	MARKING
74LVC3G04DP	-40 to +125 °C	8	TSSOP-8	plastic	SOT505-2	Y04
74LVC3G04DC	-40 to +125 °C	8	VSSOP-8	plastic	SOT765-1	Y04

PINNING

PIN	SYMBOL	DESCRIPTION
1	1A	data input 1A
2	3Y	data output 3Y
3	2A	data input 2A
4	GND	ground (0 V)
5	2Y	data output 2Y
6	3A	data input 3A
7	1Y	data output 1Y
8	V _{CC}	DC supply voltage

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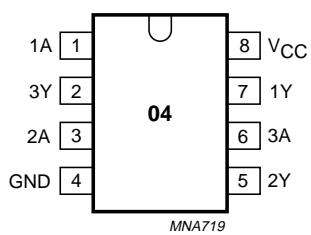


Fig.1 Pin configuration.

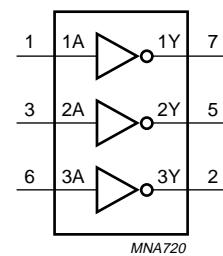


Fig.2 Logic symbol.

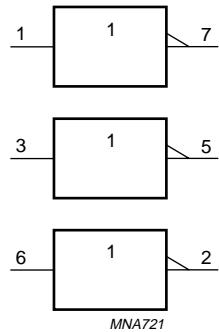


Fig.3 IEC logic symbol.

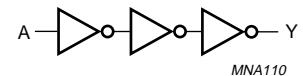


Fig.4 Logic diagram (one driver).

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RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	supply voltage		1.65	5.5	V
V_I	input voltage		0	5.5	V
V_O	output voltage	active mode	0	V_{CC}	V
		$V_{CC} = 0$ V; Power-down mode	0	5.5	V
T_{amb}	operating ambient temperature		-40	+125	°C
t_r, t_f	input rise and fall times	$V_{CC} = 1.65$ to 2.7 V	0	20	ns/V
		$V_{CC} = 2.7$ to 5.5 V	0	10	ns/V

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	supply voltage		-0.5	+6.5	V
I_{IK}	input diode current	$V_I < 0$	-	-50	mA
V_I	input voltage	note 1	-0.5	+6.5	V
I_{OK}	output diode current	$V_O > V_{CC}$ or $V_O < 0$	-	± 50	mA
V_O	output voltage	active mode; notes 1 and 2	-0.5	$V_{CC} + 0.5$	V
		Power-down mode; notes 1 and 2	-0.5	+6.5	V
I_O	output diode current	$V_O = 0$ to V_{CC}	-	± 50	mA
I_{CC}, I_{GND}	V_{CC} or GND current		-	± 100	mA
T_{stg}	storage temperature		-65	+150	°C
P_D	power dissipation per package	for temperature range from -40 to +125 °C	-	300	mW

Notes

1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. When $V_{CC} = 0$ V (Power-down mode), the output voltage can be 5.5 V in normal operation.

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DC CHARACTERISTICS

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	TEST CONDITIONS					UNIT
		OTHER	V _{CC} (V)	MIN.	TYP. ⁽¹⁾	MAX.	
Temperature range -40 to +85 °C							
V _{IH}	HIGH-level input voltage		1.65 to 1.95	0.65 × V _{CC}	—	—	V
			2.3 to 2.7	1.7	—	—	V
			2.7 to 3.6	2.0	—	—	V
			4.5 to 5.5	0.7 × V _{CC}	—	—	V
V _{IL}	LOW-level input voltage		1.65 to 1.95	—	—	0.35 × V _{CC}	V
			2.3 to 2.7	—	—	0.7	V
			2.7 to 3.6	—	—	0.8	V
			4.5 to 5.5	—	—	0.3 × V _{CC}	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} I _O = 100 µA I _O = 4 mA I _O = 8 mA I _O = 12 mA I _O = 24 mA I _O = 32 mA	1.65 to 5.5	—	—	0.1	V
			1.65	—	0.07	0.45	V
			2.3	—	0.12	0.3	V
			2.7	—	0.17	0.4	V
			3.0	—	0.33	0.55	V
			4.5	—	0.39	0.55	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} I _O = -100 µA I _O = -4 mA I _O = -8 mA I _O = -12 mA I _O = -24 mA I _O = -32 mA	1.65 to 5.5	V _{CC} - 0.1	—	—	V
			1.65	1.2	1.54	—	V
			2.3	1.9	2.15	—	V
			2.7	2.2	2.5	—	V
			3.0	2.3	2.62	—	V
			4.5	3.8	4.11	—	V
I _I	input leakage current	V _I = 5.5 V or GND	5.5	—	±0.1	±5	µA
I _{off}	power OFF leakage current	V _I or V _O = 5.5 V	0	—	±0.1	±10	µA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	—	0.1	10	µA
ΔI _{CC}	additional quiescent supply current per pin	V _I = V _{CC} - 0.6 V; I _O = 0	2.3 to 5.5	—	5	500	µA

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SYMBOL	PARAMETER	TEST CONDITIONS					UNIT
		OTHER	V _{CC} (V)	MIN.	TYP. ⁽¹⁾	MAX.	
Temperature range –40 to +125 °C							
V _{IH}	HIGH-level input voltage		1.65 to 1.95	0.65 × V _{CC}	–	–	V
			2.3 to 2.7	1.7	–	–	V
			2.7 to 3.6	2.0	–	–	V
			4.5 to 5.5	0.7 × V _{CC}	–	–	V
V _{IL}	LOW-level input voltage		1.65 to 1.95	–	–	0.35 × V _{CC}	V
			2.3 to 2.7	–	–	0.7	V
			2.7 to 3.6	–	–	0.8	V
			4.5 to 5.5	–	–	0.3 × V _{CC}	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}	1.65 to 5.5	–	0.1	V	
		I _O = 100 µA					
		I _O = 4 mA					
		I _O = 8 mA					
		I _O = 12 mA					
		I _O = 24 mA					
		I _O = 32 mA					
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}	1.65 to 5.5	V _{CC} – 0.1	–	V	
		I _O = –100 µA					
		I _O = –4 mA					
		I _O = –8 mA					
		I _O = –12 mA					
		I _O = –24 mA					
I _I	input leakage current	V _I = 5.5 V or GND	5.5	–	±0.1	±20	µA
I _{off}	power OFF leakage current	V _I or V _O = 5.5 V	0	–	–	±20	µA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	–	40	µA
ΔI _{CC}	additional quiescent supply current per pin	V _I = V _{CC} – 0.6 V; I _O = 0	2.3 to 5.5	–	–	5000	µA

Note

1. All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

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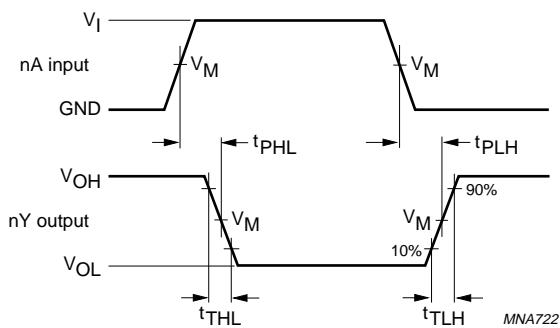
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AC CHARACTERISTICS

GND = 0 V.

SYMBOL	PARAMETER	TEST CONDITIONS		T_{amb} ($^{\circ}$ C)				UNIT	
		WAVEFORMS	V_{cc} (V)	-40 to +85			-40 to +125		
				MIN.	TYP.	MAX.	MIN.	MAX.	
t_{PHL}/t_{PLH}	propagation delay nA to nY	see Figs 5 and 6	1.65 to 1.95	1.0	3.5	8.0	1.0	9.5	ns
			2.3 to 2.7	1.0	2.2	4.4	1.0	5.4	ns
			2.7	1.0	2.7	5.2	1.0	7.0	ns
			3.0 to 3.6	0.5	2.7	4.1	0.5	5.5	ns
			4.5 to 5.5	1.0	1.9	3.2	1.0	3.8	ns

AC WAVEFORMS



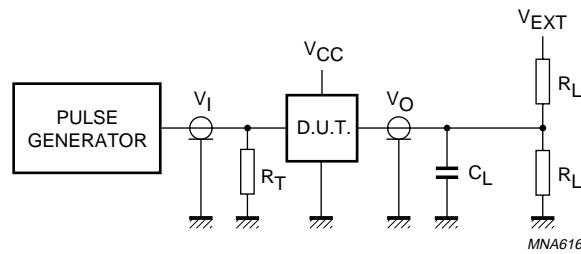
V_{cc}	V_M	INPUT	
		V_I	$t_r = t_f$
1.65 to 1.95 V	$0.5 \times V_{cc}$	V_{cc}	≤ 2.0 ns
2.3 to 2.7 V	$0.5 \times V_{cc}$	V_{cc}	≤ 2.0 ns
2.7 V	1.5 V	2.7 V	≤ 2.5 ns
3.0 to 3.6 V	1.5 V	2.7 V	≤ 2.5 ns
4.5 to 5.5 V	$0.5 \times V_{cc}$	V_{cc}	≤ 2.5 ns

V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig.5 The input (nA) to output (nY) propagation delays.

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V_{CC}	V_I	C_L	R_L	V_{EXT}		
				t_{PLH}/t_{PHL}	t_{PZH}/t_{PHZ}	t_{PZL}/t_{PLZ}
1.65 to 1.95 V	V_{CC}	30 pF	1 k Ω	open	GND	$2 \times V_{CC}$
2.3 to 2.7 V	V_{CC}	30 pF	500 Ω	open	GND	$2 \times V_{CC}$
2.7 V	2.7 V	50 pF	500 Ω	open	GND	6 V
3.0 to 3.6 V	2.7 V	50 pF	500 Ω	open	GND	6 V
4.5 to 5.5 V	V_{CC}	50 pF	500 Ω	open	GND	$2 \times V_{CC}$

Definitions for test circuit:

R_L = Load resistor.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator.

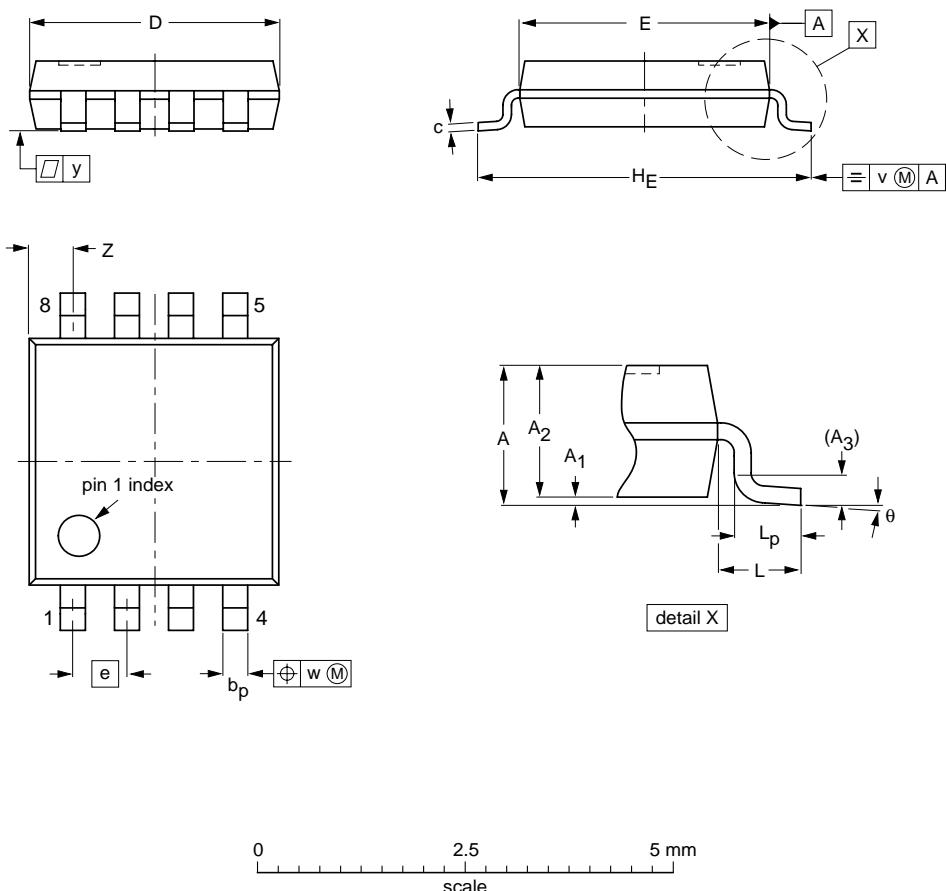
Fig.6 Load circuitry for switching times.

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PACKAGE OUTLINE

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	v	w	y	Z ⁽¹⁾	θ
mm	1.1	0.15 0.00	0.95 0.75	0.25	0.38 0.22	0.18 0.08	3.1 2.9	3.1 2.9	0.65	4.1 3.9	0.5	0.47 0.33	0.2	0.13	0.1	0.70 0.35	8° 0°

Note

- Plastic or metal protrusions of 0.15 mm maximum per side are not included.

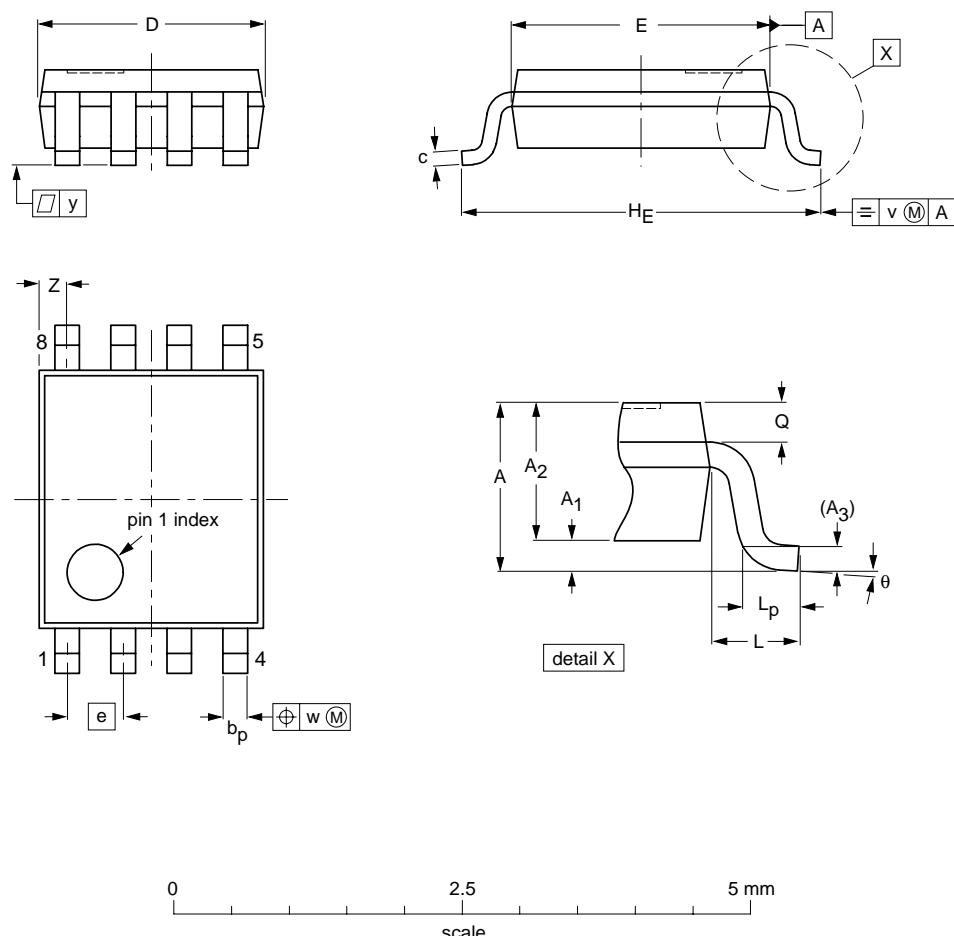
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT505-2		---				02-01-16

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VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽²⁾	e	H _E	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT765-1		MO-187				02-06-07

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DATA SHEET STATUS

DATA SHEET STATUS	PRODUCT STATUS	DEFINITIONS ⁽¹⁾
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

Note

1. Please consult the most recently issued data sheet before initiating or completing a design.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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